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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/626718
		Filing Date	July 25, 2003
		First Named Inventor	MIURA et al.
		Art Unit	Unassigned 2818
		Examiner Name	Unassigned LONG TRAN
Sheet 1 of 1	Attorney Docket Number	300.33045CC3	

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ²	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ³ (if known)				
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UPT		JP	3-96249	04/1991	Japan (Abstract only)		
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Examiner Signature	LONG TRAN	Date Considered	11/01/04
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